



HIGH FREQUENCY SECONDARY RECTIFIER

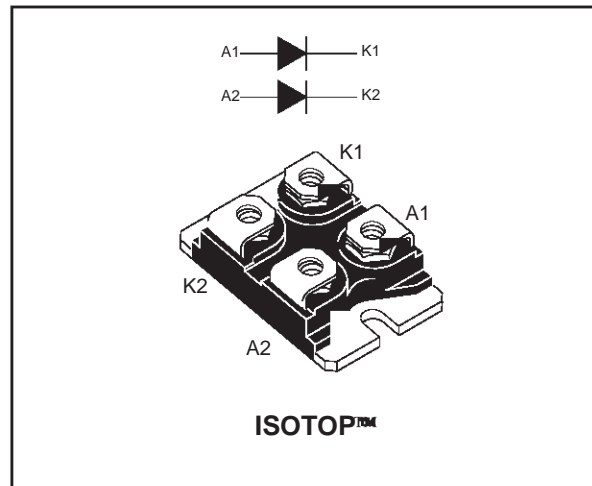
PRELIMINARY DATASHEET

MAJOR PRODUCTS CHARACTERISTICS

I_{F(AV)}	2 x 80 A
V_{RRM}	300 V
T_j (max)	175 °C
V_F (max)	0.95 V
t_{rr} (max)	80 ns

FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND VOLTAGE PERFORMANCE
- ULTRAFAST, SOFT AND NOISE-FREE RECOVERY FOR LOW SIDE EFFECTS
- ISOLATED PACKAGE:
2500 V_{RMS} (UL APPROVAL PENDING DEVICE)
- LOW INDUCTANCE AND LOW CAPACITANCE ALLOW SIMPLER LAYOUT



DESCRIPTION

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in ISOTOP™, this device is intended for use in low voltage, high frequency inverters, free wheeling operation, welding equipments and telecom power supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		300	V
I _{F(RMS)}	RMS forward current		180	A
I _{F(AV)}	Average forward current	T _c = 80°C δ = 0.5	Per diode 80 Per device 160	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	800	A
I _{RSM}	Non repetitive peak reverse current	t _p = 100 μs square	10	A
T _{stg}	Storage temperature range		- 55 to + 150	°C
T _j	Maximum operating junction temperature		150	°C

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STTH16003TV

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	Junction to case	Per diode	0.7	°C/W
		Total	0.4	
R _{th(c)}		Coupling	0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I _R *	Reverse leakage current	V _R = 300 V	T _j = 25°C			200	μA
			T _j = 125°C		0.2	2	mA
V _F **	Forward voltage drop	I _F = 80 A	T _j = 25°C			1.2	V
			T _j = 125°C		0.8	0.95	

Pulse test : * t_p = 5 ms, δ < 2 %

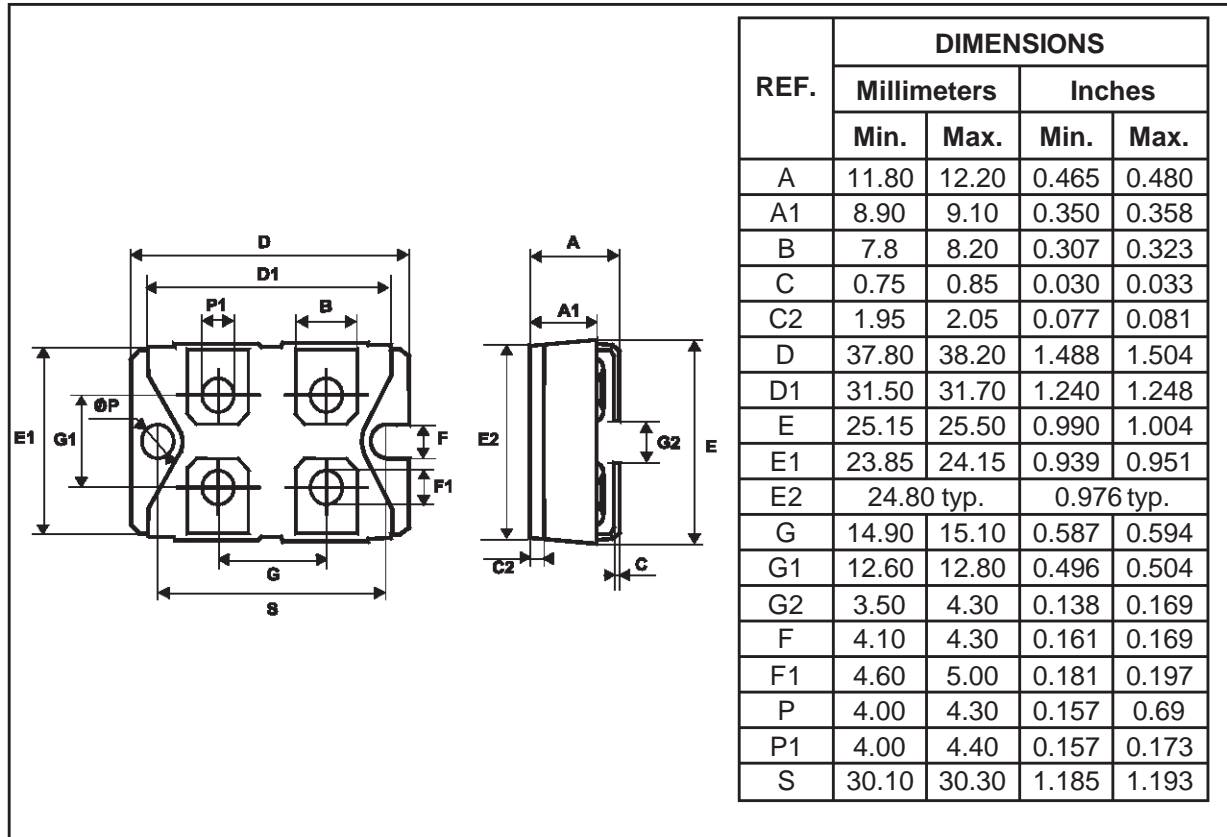
** t_p = 380 μs, δ < 2%

To evaluate the maximum conduction losses use the following equation:

$$P = 0.75 \times I_{F(AV)} + 0.0025 \times I_{F(RMS)}^2$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions			Min.	Typ.	Max.	Unit
trr	I _F = 0.5 A	I _{rr} = 0.25 A	I _R = 1 A	T _j = 25°C		60	ns
	I _F = 1 A	di _F /dt = - 50 A/μs	V _R = 30 V			80	
tfr	I _F = 80 A	di _F /dt = 200 A/μs		T _j = 25°C		1000	ns
V _{FP}	V _{FR} = 1.1 x V _F max.					5	V
S _{factor}	V _{CC} = 200 V	I _F = 80 A		T _j = 125°C		0.3	-
I _{RM}	di _F /dt = 200 A/μs						16

PACKAGE MECHANICAL DATA
 ISOTOP


- Cooling method: by conduction (C)
- Recommended torque value : 1.3 N.m.
- Maximum torque value: 1.5 N.m.

Type	Marking	Package	Weight	Base qty	Delivery mode
STTH16003TV1	STTH16003TV	ISOTOP	27 g without screws	10 with screws	Tube

- Epoxy meets UL 94,V0

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